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# Contents

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<b>PREFACE</b> . . . . .	xi
<b>PART 1. GaN AND ZnO NANOWIRES: LOW-DIMENSIONALITY EFFECTS</b> . . . . .	1
<b>CHAPTER 1. QUANTUM AND OPTICAL CONFINEMENT</b> . . . . .	3
Le Si DANG	
1.1. Introduction. . . . .	3
1.2. All-optical integrated circuits with Bose exciton polaritons . . . . .	4
1.3. High efficiency single photon sources . . . . .	9
1.4. High efficiency solar photovoltaics. . . . .	14
1.4.1. Potential photovoltaic benefits of the nanowire geometry . . . . .	14
1.4.2. Interests of wide band gap semiconductor photovoltaics. . . . .	17
1.5. Conclusion . . . . .	18
1.6. Bibliography . . . . .	18
<b>CHAPTER 2. STRESS RELAXATION IN NANOWIRES WITH HETEROSTRUCTURES</b> . . . . .	25
Frank GLAS	
2.1. Introduction. . . . .	25
2.1.1. Scope . . . . .	25
2.1.2. Stress relaxation. . . . .	26
2.1.3. Nanowire specificities . . . . .	27
2.2. Calculation and measurement of elastic strain in nanowires . . . . .	28
2.2.1. Calculation of elastic strain . . . . .	28
2.2.2. Measurement of elastic strain. . . . .	29
2.3. Core-shell heterostructures. . . . .	30
2.3.1. Elastic relaxation in core-shell heterostructures . . . . .	30

2.3.2. Plastic relaxation and critical parameters in core-shell heterostructures . . . . .	33
2.4. Axial heterostructures. . . . .	39
2.4.1. Elastic relaxation in axial heterostructures . . . . .	39
2.4.2. Critical dimensions for axial heterostructures . . . . .	43
2.5. Other possible modes of stress relaxation in nanowires with heterostructures . . . . .	48
2.6. Summary and conclusions . . . . .	49
2.7. Bibliography . . . . .	50
<b>CHAPTER 3. SURFACE-RELATED OPTICAL PROPERTIES OF GaN-BASED NANOWIRES . . . . .</b>	<b>59</b>
Pierre LEFEBVRE	
3.1. Introduction. . . . .	59
3.2. Specific exciton and donor states related to surfaces . . . . .	60
3.3. Non-radiative surface recombination. . . . .	69
3.4. Influence of surface photochemical activity on nitride nanowire optical properties . . . . .	72
3.5. Summary . . . . .	75
3.6. Bibliography . . . . .	76
<b>CHAPTER 4. SURFACE RELATED OPTICAL PROPERTIES OF ZnO NANOWIRES . . . . .</b>	<b>81</b>
Tobias VOSS and Jürgen GUTOWSKI	
4.1. Introduction. . . . .	81
4.2. Surface excitons in ZnO nanowires. . . . .	83
4.3. Surface-related defect luminescence in ZnO nanowires. . . . .	88
4.4. Surface functionalization of ZnO nanowires with colloidal quantum dots . . . . .	91
4.5. Other surface-related effects in ZnO nanowires . . . . .	95
4.6. Conclusion . . . . .	96
4.7. Bibliography . . . . .	97
<b>CHAPTER 5. DOPING AND TRANSPORT . . . . .</b>	<b>99</b>
Julien PERNOT, Fabrice DONATINI and Pierre TCHOULFIAN	
5.1. Introduction. . . . .	99
5.2. Advanced lithography processes for direct wide band gap nanowire and microwire devices . . . . .	100
5.3. Electrical transport properties of single wire: ZnO nanowire and GaN microwire. . . . .	105
5.3.1. Electrical transport measurements . . . . .	105
5.3.2. Mobility versus doping . . . . .	114

---

5.4. Local probe and mapping of the electric field: cathodoluminescence. . .	116
5.5. Conclusion and perspectives. . . . .	119
5.6. Bibliography . . . . .	120
<b>CHAPTER 6. MICROSTRUCTURE OF GROUP III-N NANOWIRES . . . . .</b>	<b>125</b>
Achim TRAMPERT, Xiang KONG, Esperanza LUNA, Javier GRANDAL and Bernd JENICHEN	
6.1. Introduction. . . . .	125
6.2. Structural properties. . . . .	126
6.2.1. Crystal structure. . . . .	126
6.2.2. Nanowire morphology . . . . .	129
6.2.3. Macroscopic and microscopic strain. . . . .	132
6.3. Polarity . . . . .	134
6.4. Extended defects in nanowires . . . . .	139
6.4.1. Stacking faults. . . . .	140
6.4.2. Inversion domain boundaries . . . . .	143
6.5. Interfaces and heterostructures . . . . .	145
6.5.1. Interface between III-N nanowire and substrate . . . . .	145
6.5.2. Axial nanowire heterostructure: (In,GaN)/GaN case study . . . . .	150
6.6. Conclusions. . . . .	152
6.7. Bibliography . . . . .	153
<b>PART 2. NUCLEATION AND GROWTH MECHANISMS OF GaN AND ZnO NANOWIRES . . . . .</b>	<b>157</b>
<b>CHAPTER 7. Ni COLLECTOR-INDUCED GROWTH OF GaN NANOWIRES ON C-PLANE SAPPHIRE BY PLASMA-ASSISTED MOLECULAR BEAM EPITAXY . . . . .</b>	<b>159</b>
Caroline CHÈZE	
7.1. Introduction. . . . .	159
7.2. Experimental description. . . . .	160
7.3. Ni-induced GaN nanowire nucleation . . . . .	162
7.4. Ni-induced GaN nanowire growth mechanism . . . . .	167
7.5. Ni-induced GaN nanowire structural and optical properties . . . . .	169
7.6. Conclusion . . . . .	173
7.7. Acknowledgments . . . . .	173
7.8. Bibliography . . . . .	174
<b>CHAPTER 8. SELF-INDUCED GROWTH OF GaN NANOWIRES BY MOLECULAR BEAM EPITAXY . . . . .</b>	<b>177</b>
Vincent CONSONNI	
8.1. Introduction. . . . .	177

8.2. General principles . . . . .	178
8.2.1. MBE chamber . . . . .	178
8.2.2. Typical growth conditions. . . . .	179
8.2.3. Nucleation surface effects. . . . .	180
8.3. Nucleation phase. . . . .	183
8.3.1. Incubation period . . . . .	184
8.3.2. Transition period . . . . .	188
8.4. Growth phase. . . . .	191
8.4.1. Elongation period. . . . .	191
8.4.2. Radial growth . . . . .	197
8.4.3. Coalescence period. . . . .	200
8.4.4. Density effects . . . . .	202
8.4.5. Polarity effects . . . . .	203
8.5. Conclusion . . . . .	205
8.6. Acknowledgments. . . . .	206
8.7. Bibliography . . . . .	206
<b>CHAPTER 9. SELECTIVE AREA GROWTH OF GaN NANOWIRES BY PLASMA-ASSISTED MOLECULAR BEAM EPITAXY . . . . .</b>	<b>215</b>
Miguel A. SANCHEZ-GARCIA, Steven ALBERT, Ana M. BENGOCHEA-ENCABO, Francesca BARBAGINI and Enrique CALLEJA	
9.1. Introduction. . . . .	215
9.2. Mask preparation . . . . .	216
9.3. Selectivity, nucleation mechanism and morphology control of the nanocolumns . . . . .	220
9.4. Growth of ordered nanocolumns for LEDs applications . . . . .	225
9.4.1. InGaN with single color emission . . . . .	225
9.4.2. InGaN with a gradient In composition for white light emission . . . . .	230
9.4.3. Red, green, blue structures for white light emission . . . . .	232
9.5. Growth of ordered GaN nanocolumns on non-polar and semi-polar directions . . . . .	234
9.6. Summary . . . . .	238
9.7. Bibliography . . . . .	239
<b>CHAPTER 10. METAL-ORGANIC VAPOR PHASE EPITAXY GROWTH OF GaN NANORODS . . . . .</b>	<b>245</b>
Joël EYMERY	
10.1. Introduction . . . . .	245
10.2. Catalyst-assisted growth . . . . .	247
10.3. Catalyst-free and self-organized growth . . . . .	249
10.4. Selected-area growth . . . . .	254

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10.5. Discussion and conclusion . . . . .	257
10.6. Bibliography . . . . .	257
<b>CHAPTER 11. METAL-ORGANIC CHEMICAL VAPOR DEPOSITION GROWTH OF ZnO NANOWIRES . . . . .</b>	<b>265</b>
Vincent SALLET	
11.1. Introduction . . . . .	265
11.2. Thermodynamics . . . . .	266
11.3. Growth of ZnO nanowires . . . . .	268
11.4. Spontaneous growth of ZnO nanowires: growth condition effects. . . . .	271
11.4.1. O/Zn ( $R_{VI/II}$ ) ratio . . . . .	272
11.4.2. Substrates . . . . .	275
11.4.3. Growth temperature. . . . .	276
11.4.4. Pressure . . . . .	278
11.4.5. Supersaturation and growth rate . . . . .	279
11.4.6. Structural characterization and growth mechanisms. . . . .	280
11.5. Selective area growth of ZnO nanowires. . . . .	285
11.6. Catalyst-assisted growth of ZnO nanowires . . . . .	286
11.6.1. Evidence of the catalytic effect . . . . .	288
11.6.2. MOCVD growth of catalyst-assisted ZnO nanowires. . . . .	288
11.6.3. Formation of ZnO nanoribbons . . . . .	291
11.6.4. Discussion of the catalyzed-growth mechanisms: VLS or not? . . . . .	292
11.6.5. Polarity of VLS grown ZnO nanowires . . . . .	295
11.7. Acknowledgements . . . . .	297
11.8. Bibliography . . . . .	297
<b>CHAPTER 12. PULSED-LASER DEPOSITION OF ZnO NANOWIRES . . . . .</b>	<b>303</b>
Christoph Peter DIETRICH and Marius GRUNDMANN	
12.1. Introduction . . . . .	303
12.2. Principles of high-pressure and hot-walled pulsed-laser deposition. . . . .	304
12.3. Tuning the nanowire morphology . . . . .	306
12.4. Doped binary nanowires and ternary alloy nanowires . . . . .	309
12.5. Fabrication of nanowire heterostructures. . . . .	312
12.6. Summary and outlook . . . . .	319
12.7. Bibliography . . . . .	319
<b>CHAPTER 13. PREPARATION OF ZnO NANORODS AND NANOWIRES BY WET CHEMISTRY. . . . .</b>	<b>325</b>
Thierry PAUपोर्टÉ	
13.1. Introduction . . . . .	325

13.2. Preparation of ZnO nanorods and nanowires by chemical bath deposition and hydrothermal techniques . . . . .	326
13.2.1. Principle . . . . .	326
13.2.2. Growth of ZnO nanostructure in bulk solution . . . . .	327
13.2.3. Chemical growth of ZnO nanowire/nanorod arrays on substrate . . . . .	334
13.3. Preparation of ZnO nanorods and nanowires by electrodeposition . . . . .	347
13.3.1. Principles of ZnO electrodeposition . . . . .	347
13.3.2. ZnO growth mechanism . . . . .	348
13.3.3. Electrochemical growth of ZnO nanorod and nanowire arrayed layers . . . . .	355
13.3.4. Substrate surface treatment and seed layers. . . . .	359
13.3.5. Electrochemical growth of ZnO nanowires on templates. . . . .	360
13.3.6. Effect of electrochemical bath composition and use of cation additives for doping . . . . .	362
13.4. Applications of ZnO nanorods/nanowires prepared by wet chemistry and by electrochemistry. . . . .	364
13.5. Conclusions . . . . .	366
13.6. Bibliography . . . . .	366
<b>LIST OF AUTHORS . . . . .</b>	<b>379</b>